

DC and RF Characterization Data Kurt Lesker PVD 75

Note: Please use this data as guidance, some further characterization might be required

<p>SnO₂ Source Diameter: 4" Film Thickness: 60 nm Baseline pressure: 2e-6 Torr RF Power: 300 W Deposition Time: 6 min Gas Pressure: Argon, 12.75 mTorr</p>	<p>Ti/Pt Source Diameters: ? Film Thickness: 100 nm Baseline pressure: 1.3e-6 Torr DC Power: 300 W Deposition Time: 2 min / 3 min Gas Pressure: Argon, 5 mTorr</p>
<p>Cr/Au Source Diameters: 4"/3" Film Thickness: 360 nm Baseline pressure: 1.3e-6 Torr DC Power: 300 W Deposition Time: 2 min / 6 min Gas Pressure: Argon, 5 mTorr</p>	<p>Ta Source Diameters: 3" Film Thickness: 43 nm Baseline pressure: 3.0e-6 Torr DC Power: 200 W Deposition Time: 5 min Gas Pressure: Argon, 5 mTorr</p>
<p>Al Source Diameter: ? Film Thickness: 303 nm Baseline pressure: 1.5e-6 Torr DC Power: 300 W Deposition Time: 40 min Gas Pressure: Argon, 5 mTorr</p>	<p>Al Source Diameter: ? Film Thickness: 100 nm Baseline pressure: 1.5e-6 Torr DC Power: 500 W Deposition Time: 5 min Gas Pressure: Argon, 5 mTorr</p>
<p>Al (low stress) Source Diameter: ? Film Thickness: 170 nm Baseline pressure: 5e-6 Torr DC Power: 600 W Deposition Time: 20 min Gas Pressure: Argon, 25 mTorr</p>	<p>Sn Source Diameter: ? Film Thickness: 303 nm Baseline pressure: 1.5e-6 Torr DC Power: 300 W Deposition Time: 40 min Gas Pressure: Argon, 5 mTorr</p>
<p>Cu Source Diameter: 4" Film Thickness: 50 nm Baseline pressure: 2.2e-6 Torr DC Power: 40 W</p>	<p>Ni Source Diameter: 4" Film Thickness: 50 nm Baseline pressure: 2.3e-6 Torr DC Power: 300 W</p>

<p>Deposition Time: 20 min Gas Pressure: Argon, 5 mTorr</p>	<p>Deposition Time: 7 min Gas Pressure: Argon, 5 mTorr</p>
<p>Cr Source Diameter: ? Film Thickness: 200 nm Baseline pressure: 2.1e-6 Torr DC Power: 300 W Deposition Time: 13 min Gas Pressure: Argon, 5 mTorr</p>	<p>TiW Source Diameter: 3" Film Thickness: 90 nm Baseline pressure: 1.0e-7 Torr DC Power: 300 W Deposition Time: 20 min Gas Pressure: Argon, 5 mTorr</p>
<p>Ti Source Diameter: ? Film Thickness: 80 nm Baseline pressure: 5e-6 Torr DC Power: 300 W Deposition Time: 10 min Gas Pressure: Argon, 5 mTorr</p>	<p>Fe₂O₃ Source Diameter: 4" Film Thickness: 47 nm Baseline pressure: 1.1e-6 Torr RF Power: 200 W Deposition Time: 15 min Gas Pressure: Argon, 12 mTorr</p>
<p>SnO₂ (Reactive from the Sn target) Source Diameters: 3" Film Thickness: 160 nm Baseline pressure: 4e-7 Torr DC Power: 75 W Deposition Time: 20 min Gas Pressure: Argon + O₂ 30% 10 mTorr</p>	